





EH25 00

Series —
RoHS Compliant (Pb-free) 5.0V 4 Pad 5mm x 7mm
Ceramic SMD HCMOS/TTL High Frequency Oscillator

Frequency Tolerance/Stability ±100ppm Maximum

Operating Temperature Range – 0°C to +70°C

TS -33.333M

Nominal Frequency 33.333MHz

Pin 1 Connection
Tri-State (High Impedance)

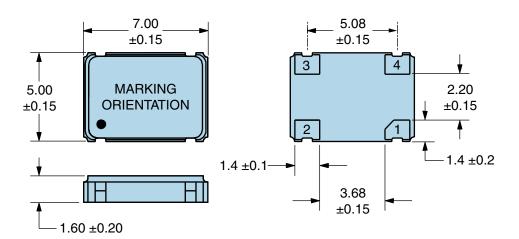
Duty Cycle 50 ±10(%)

Opera Shock ging at 25°C ±5ppn perating Temperature Range 0°C to upply Voltage 5.0Vd put Current 50mA utput Voltage Logic High (Voh) 2.4Vd utput Voltage Logic Low (Vol) 0.4Vd ise/Fall Time 6nSec with H uty Cycle 50 ±10		
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put Current 5.0Vd  put Current 50mA  utput Voltage Logic High (Voh) 2.4Vd  utput Voltage Logic Low (Vol) 0.4Vd  ise/Fall Time 6nSec  with H  uty Cycle 50 ±10	m/year Maximum	
put Current 50mA utput Voltage Logic High (Voh) 2.4Vd utput Voltage Logic Low (Vol) 0.4Vd ise/Fall Time 6nSec with H uty Cycle 50 ±10	o +70°C	
utput Voltage Logic High (Voh)  2.4Vdu utput Voltage Logic Low (Vol)  ise/Fall Time  6nSec with H  uty Cycle  50 ±10	lc ±10%	
utput Voltage Logic Low (Vol)         0.4Vdd           ise/Fall Time         6nSec           utp Cycle         50 ±10	Maximum (No Load)	
ise/Fall Time 6nSec with H uty Cycle 50 ±10	lc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)	
with H uty Cycle 50 ±10	lc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOH= +16mA)	
• •	c Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform HCMOS Load)	
pad Drive Capability 10TTL	0(%) (Measured at 1.4Vdc with TTL Load; Measured at 50% of waveform with HCMOS Load)	
	L Load or 50pF HCMOS Load Maximum	
utput Logic Type CMOS	S	
n 1 Connection Tri-Sta	ate (High Impedance)	
	dc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to e output.	
bsolute Clock Jitter ±250p	oSec Maximum, ±100pSec Typical	
ne Sigma Clock Period Jitter ±50pS	±50pSec Maximum, ±30pSec Typical	
art Up Time 10mS	Sec Maximum	
orage Temperature Range -55°C	to +125°C	

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS		
ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	sisture Sensitivity J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	



### **MECHANICAL DIMENSIONS (all dimensions in millimeters)**



PIN	CONNECTION
1	Tri-State
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	33.333M
3	XXXXXX XXXXX=Ecliptek Manufacturing Identifier

#### **Suggested Solder Pad Layout**

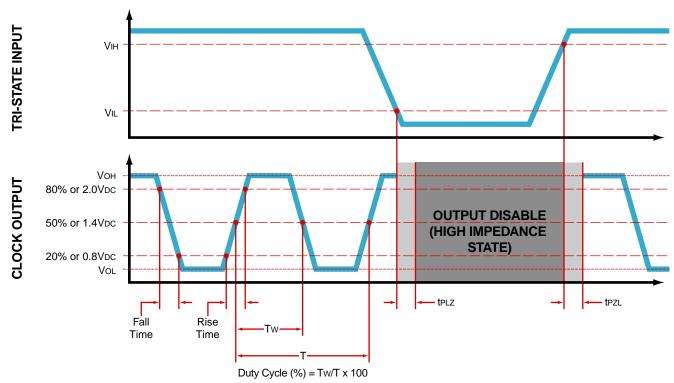
All Dimensions in Millimeters



All Tolerances are ±0.1



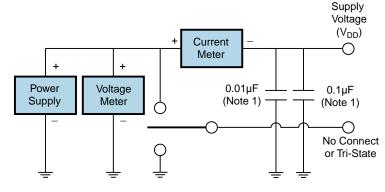
#### **OUTPUT WAVEFORM & TIMING DIAGRAM**

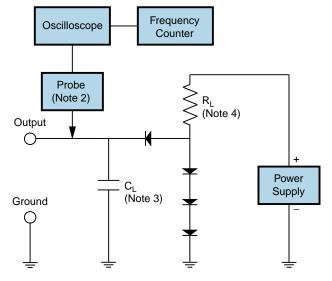


#### **Test Circuit for TTL Output**

Output Load Drive Capability	R <sub>L</sub> Value (Ohms)	C <sub>L</sub> Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1:  $R_L$  Resistance Value and  $C_L$  Capacitance Value Vs. Output Load Drive Capability





Note 1: An external  $0.1\mu F$  low frequency tantalum bypass capacitor in parallel with a  $0.01\mu F$  high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $C_{\mathsf{L}}$  includes sum of all probe and fixture capacitance.

Note 4: Resistance value R<sub>L</sub> is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



### **Test Circuit for CMOS Output**



Note 1: An external  $0.1\mu F$  low frequency tantalum bypass capacitor in parallel with a  $0.01\mu F$  high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $\dot{C}_L$  includes sum of all probe and fixture capacitance.



# **Recommended Solder Reflow Methods**

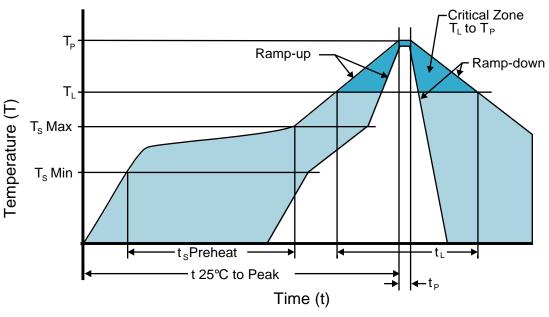


### **High Temperature Infrared/Convection**

3°C/second Maximum
150°C
175°C
200°C
60 - 180 Seconds
3°C/second Maximum
217°C
60 - 150 Seconds
260°C Maximum for 10 Seconds Maximum
250°C +0/-5°C
20 - 40 seconds
6°C/second Maximum
8 minutes Maximum
Level 1
Temperatures shown are applied to body of device.



## **Recommended Solder Reflow Methods**



### Low Temperature Infrared/Convection 240°C

T <sub>S</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	N/A
- Temperature Typical (T <sub>S</sub> TYP)	150°C
- Temperature Maximum (T <sub>s</sub> MAX)	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T <sub>P</sub> )	240°C Maximum
Target Peak Temperature (T <sub>P</sub> Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

### **Low Temperature Manual Soldering**

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)